

DATA SHEET

**ELECTROSTATIC DISCHARGE
PROTECTION DEVICES**

INDUSTRIAL / CONSUMER

SDT23C712L02

RoHS compliant & Halogen free



Product specification— March 20, 2021 V.2



Electrostatic Discharge Protection Devices (ESD) Data Sheet

Description

Brightking's SDT23C712L02 component is designed for asymmetrical (12V to -7V) protection in multi-point data transmission standard RS-485 applications. It may be used to protect devices from transient voltages resulting from electrostatic discharge (ESD), electrical fast transients (EFT), and lightning. It features 400W ($t_p=8/20\mu s$) of power handling capability to accommodate the higher transient voltage levels which may be expected in extended common mode applications.

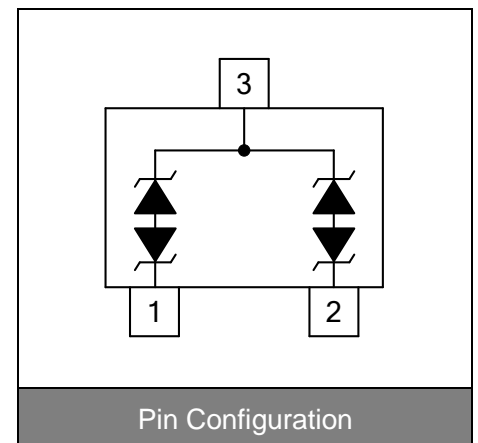


Contact : $\pm 30kV$
Air : $\pm 30kV$



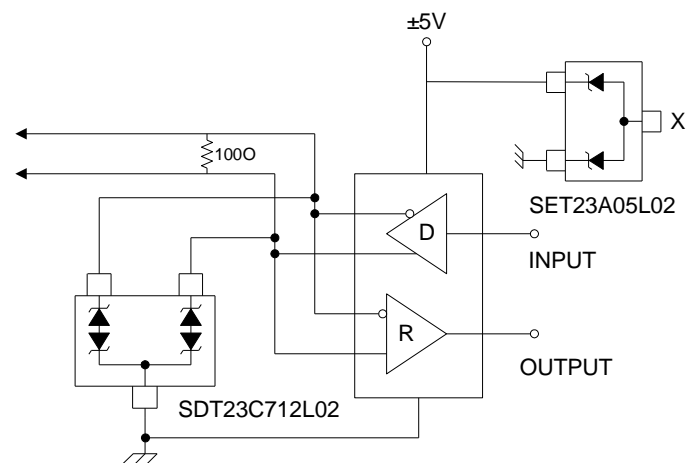
Features

- IEC61000-4-2 ESD 30KV Air, 30KV contact compliance
- SOT-23 surface mount package
- Protects two +12V to -7V lines
- Peak power dissipation of 400W under 8/20 μs waveform
- Low leakage current
- Low clamping voltage
- Solid-state silicon avalanche technology
- Lead Free/RoHS compliant
- Solder reflow temperature: Pure Tin-Sn, 260~270°C
- Flammability rating UL 94V-0
- Meets MSL level 1, per J-STD-020
- Marking: B 712



Applications

- Protection of RS-485 transceiver with extended Common-mode range
- Security Systems
- Automatic Teller Machines
- HFC Systems
- Networks



Maximum Ratings

Rating	Symbol	Value	Unit
Peak pulse power (tp=8/20μs waveform)	P _{PP}	400	W
ESD voltage (Contact discharge)	V _{ESD}	±30	kV
ESD voltage (Air discharge)		±30	
Storage & operating temperature range	T _{STG} , T _J	-55~+150	°C

Electrical Characteristics (T_J=25°C)

Pin 1 to Pin3 and Pin2 to Pin3

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse stand-off voltage	V _{RWM}				12	V
Reverse breakdown voltage	V _{BR}	I _{BR} =1mA	13.3			V
Reverse leakage current	I _R	V _R =12V			1	μA
Clamping voltage (tp=8/20μs)	V _C	I _{PP} =5A			20	V
Peak Pulse Current(tp=8/20μs)	I _{PP}				15	A
Off state junction capacitance	C _J	0Vdc, f=1MHz Between I/O pins and GND			75	pF

Pin 3 to Pin1 and Pin3 to Pin2

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse stand-off voltage	V _{RWM}				7	V
Reverse breakdown voltage	V _{BR}	I _{BR} =1mA	7.5			V
Reverse leakage current	I _R	V _R =7V			20	μA
Clamping voltage (tp=8/20μs)	V _C	I _{PP} =5A			10	V
Peak Pulse Current(tp=8/20μs)	I _{PP}				15	A
Off state junction capacitance	C _J	0Vdc, f=1MHz Between I/O pins and GND			75	pF

Typical Characteristics Curves

Figure 1. Power Derating Curve

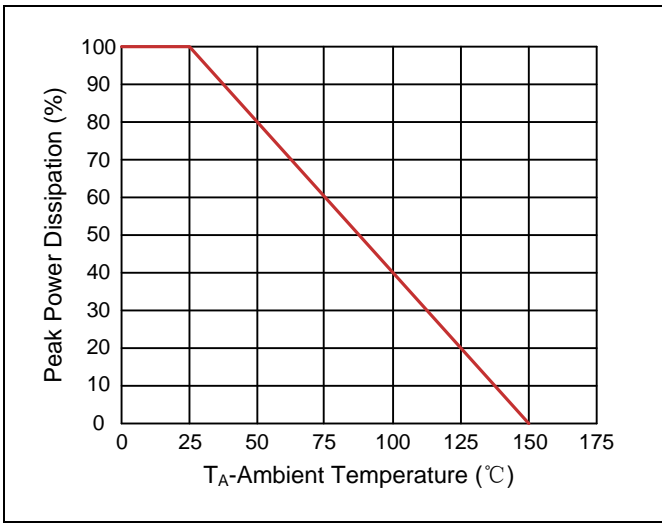


Figure 2. Pulse Waveforms

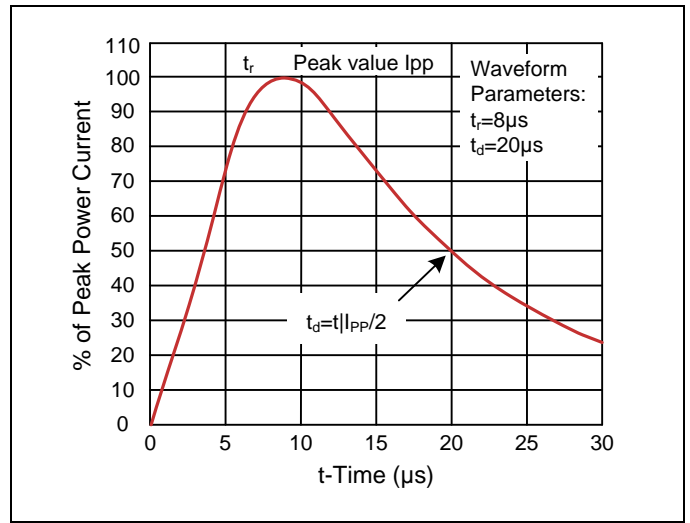


Figure 3. Non-Repetitive Peak Pulse vs. Pulse Time

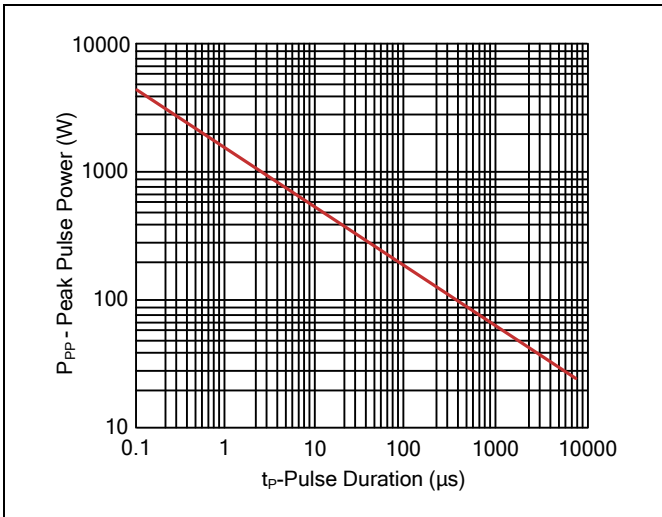
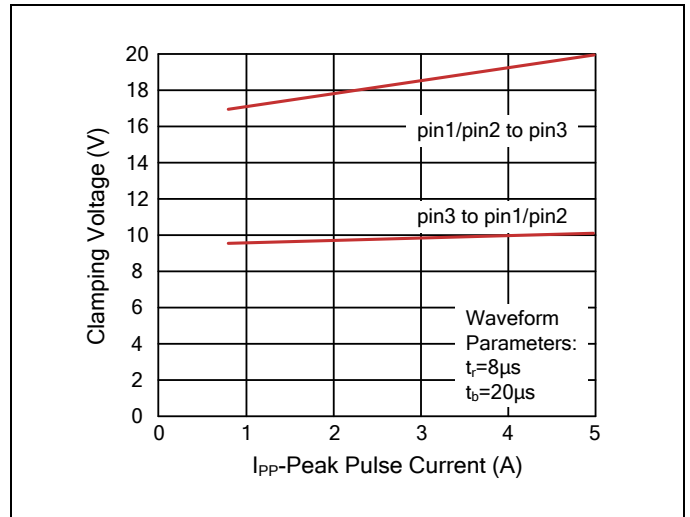
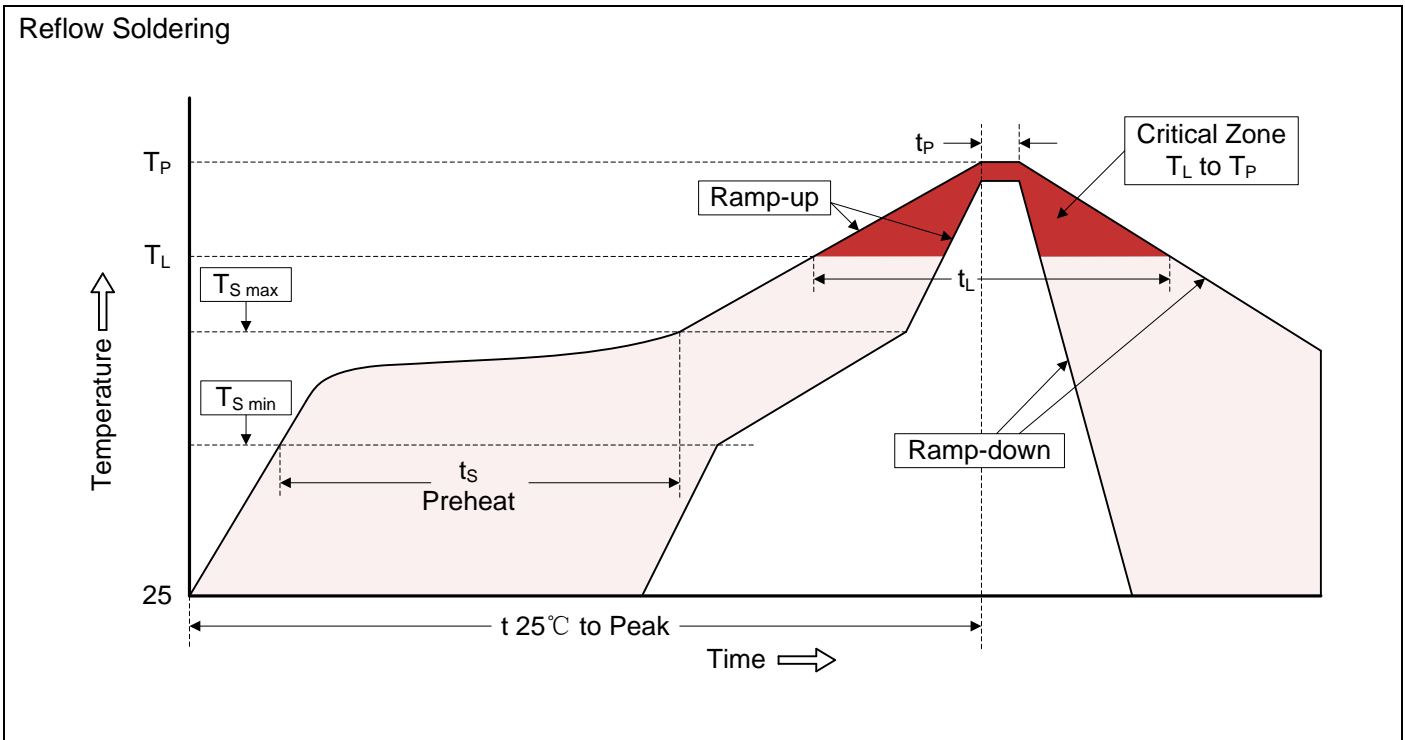


Figure 4. Clamping Voltage vs. Peak Pulse Current



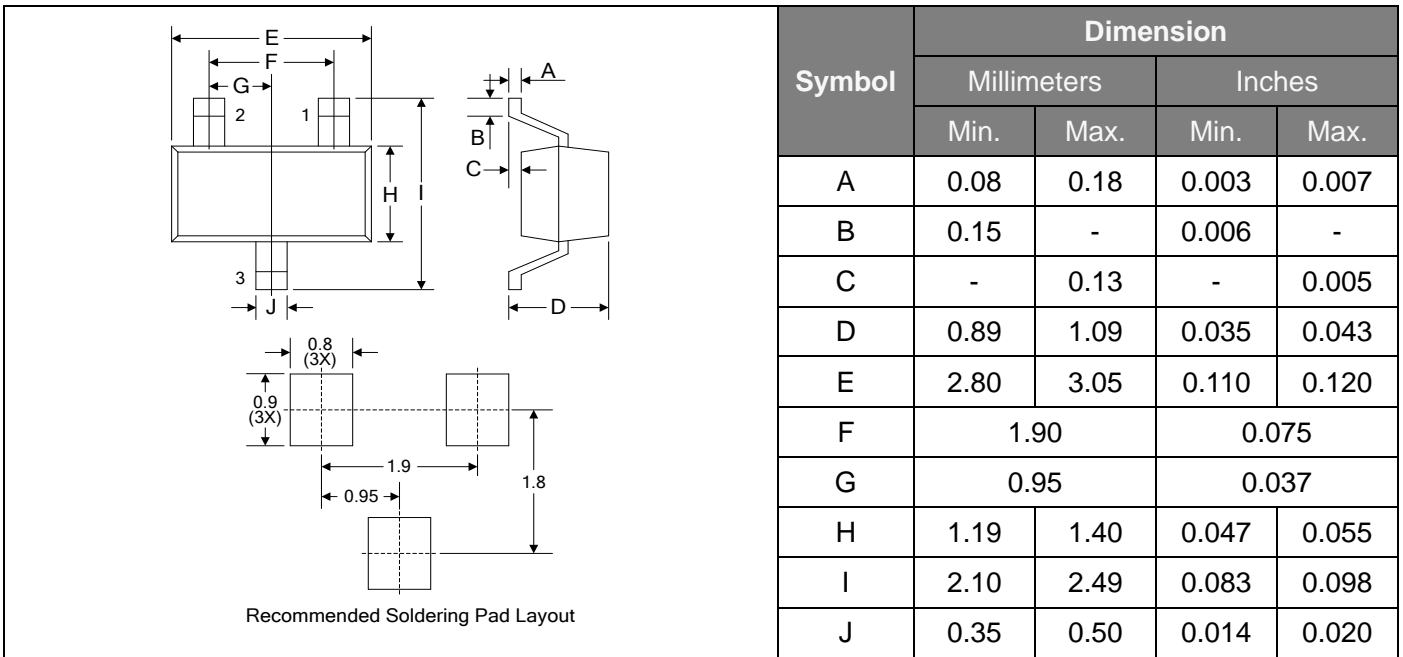
Recommended Soldering Conditions



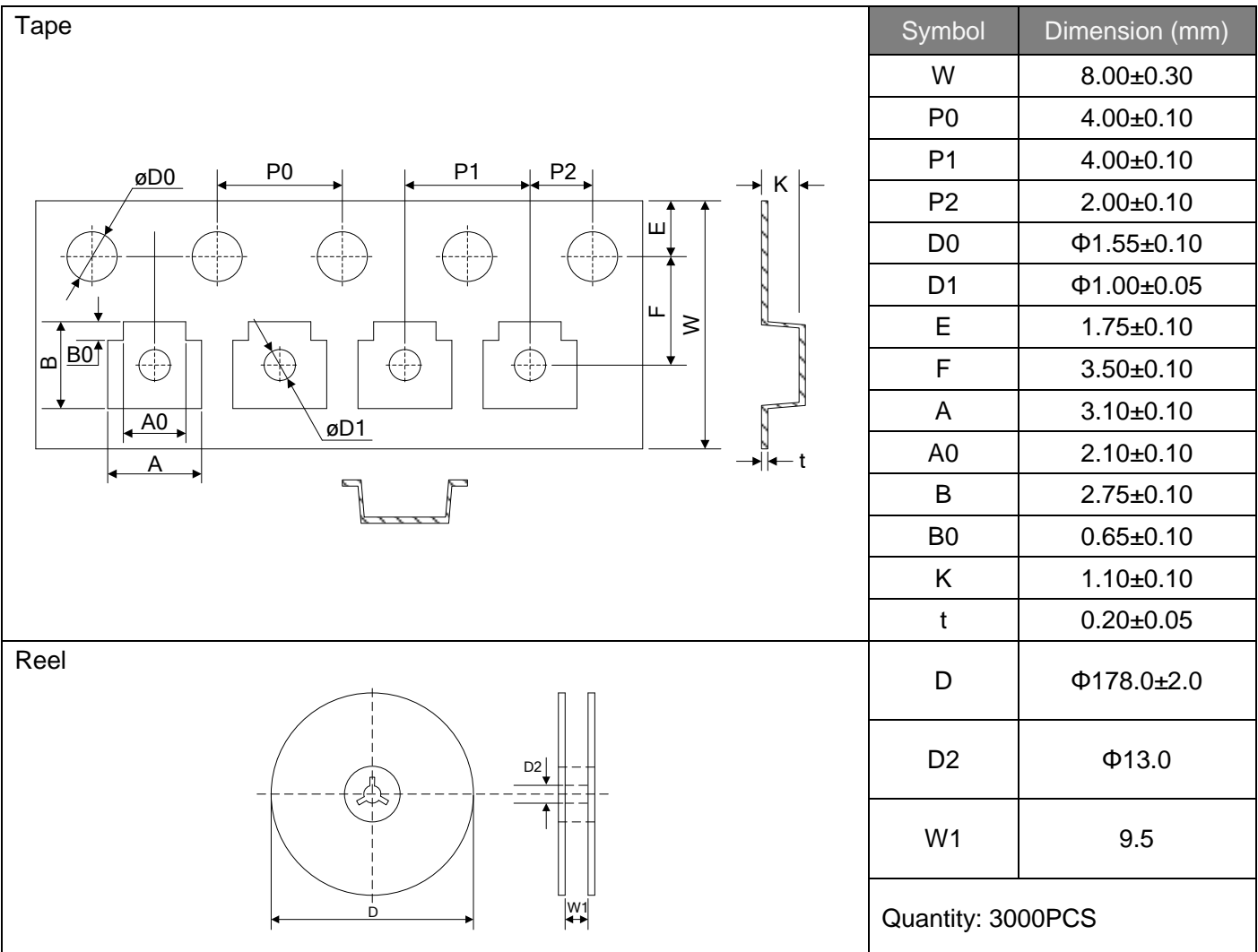
Recommended Conditions

Profile Feature	Pb-Free Assembly
Average ramp-up rate (T_L to T_P)	3°C/second max.
Preheat	150°C
-Temperature Min ($T_{S\ min}$)	200°C
-Temperature Max ($T_{S\ max}$)	60-180 seconds
-Time (min to max) (t_s)	
$T_{S\ max}$ to T_L	
-Ramp-up Rate	3°C/second max.
Time maintained above:	
-Temperature (T_L)	217°C
-Time (t_L)	60-150 seconds
Peak Temperature (T_P)	260°C
Time within 5°C of actual Peak Temperature (t_P)	20-40 seconds
Ramp-down Rate	6°C/second max.
Time 25°C to Peak Temperature	8 minutes max.

Dimensions (SOT-23)



Packaging



单击下面可查看定价，库存，交付和生命周期等信息

[>>Brightking\(君耀电子\)](#)